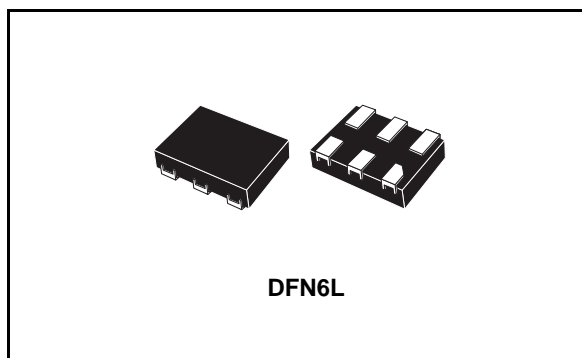


Low voltage 1 Ω single SPDT switch with break-before-make feature

Features

- High speed:
 - $t_{PD} = 130$ ps (typ.) at $V_{CC} = 3.0$ V
 - $t_{PD} = 140$ ps (typ.) at $V_{CC} = 2.3$ V
- Ultra low power dissipation:
 - $I_{CC} = 0.2$ μ A (max.) at $T_A = 85$ °C
- Low ON resistance:
 - $R_{ON} = 1.0$ Ω (Typ.) at $V_{CC} = 4.5$ V
 - $R_{ON} = 1.2$ Ω (Typ.) at $V_{CC} = 3.0$ V
 - $R_{ON} = 2.0$ Ω (Typ.) at $V_{CC} = 1.8$ V
- Wide operating voltage range:
 - V_{CC} (opr) = 1.65 to 4.5 V single supply
- 5 V tolerant and 1.8 V compatible threshold on digital control input at $V_{CC} = 1.65$ to 4.5 V
- Latch-up performance exceeds 200 mA per JESD 78, Class II
- ESD performance tested per JESD22
 - 2000 V human-body model (A114-B, Class II)
 - 200 V machine model (A115-A)
 - 1000 V charged-device model (C101)



Description

The STG5123 is a high-speed CMOS low voltage single analog SPDT (single-pole dual-throw) switch or 2:1 multiplexer/demultiplexer switch fabricated using silicon gate C²MOS technology. Designed to operate from 1.65 to 4.5 V, this device is ideal for portable applications.

The device offers very low ON resistance (1 Ω) at $V_{CC} = 4.5$ V. The switch S1 is ON (connected to common ports Dn) when the SEL input is held high and OFF (state of high impedance state exists between the two ports) when SEL is held low. The switch S2 is ON (connected to common port D) when the SEL input is held low and OFF (state of high impedance state exists between the two ports) when SEL is held high.

Additional key features are fast switching speed, break-before-make delay time and ultra low power consumption. All inputs and outputs are equipped with protection circuits against static discharge, giving them ESD and transient excess voltage immunity.

Table 1. Device summary

Order code	Package	Packaging
STG5123DTR	DFN6L (1.2 x 1 mm)	Tape and reel

Contents

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3.2	AC electrical characteristics	7
3.3	Analog switch characteristics	8
4	Test circuits	9
5	Package mechanical data	13
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1 Pin connections and functions

Figure 1. Pin connections (top through view)

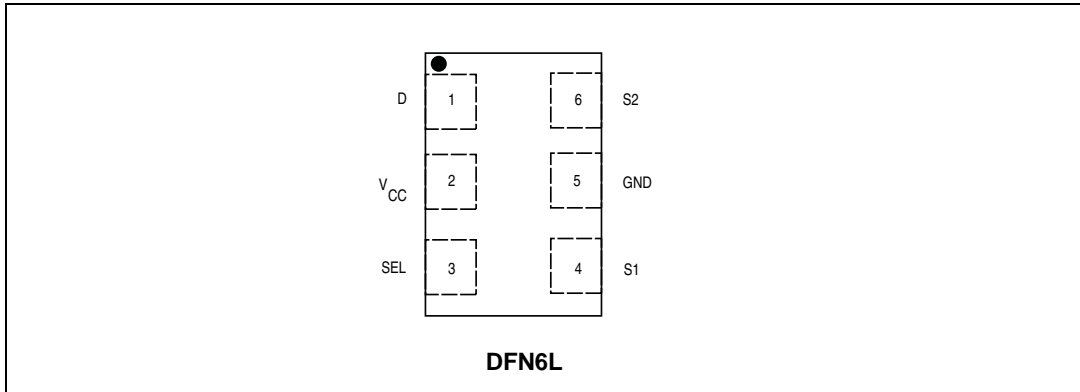


Table 2. Pin descriptions

Pin number	Symbol	Name and function
4	S1	Independent channel
6	S2	Independent channel
1	D	Common channels
3	SEL	Control
2	V _{CC}	Positive supply voltage
5	GND	Ground (0V)

Figure 2. Input equivalent circuit

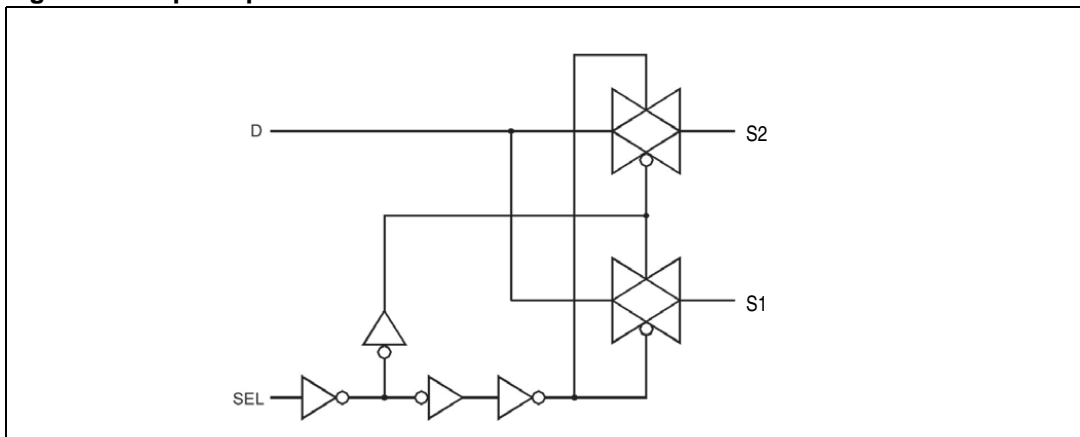


Table 2. Truth table

Sel	Switch S1	Switch S2
H	ON	OFF ⁽¹⁾
L	OFF ⁽¹⁾	ON

1. High impedance

2 Electrical ratings

Stressing the device above the rating listed in the “Absolute maximum ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	-0.5 to 5.5	V
V_I	DC input voltage	-0.5 to $V_{CC} + 0.5$	V
V_{IC}	DC control input voltage	-0.5 to 5.5	V
V_O	DC output voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IKC}	DC input diode current on control pin ($V_{SEL} < 0$ V)	-50	mA
I_{IK}	DC input diode current ($V_{IN} < 0$ V)	± 50	mA
I_{OK}	DC output diode current	± 20	mA
I_O	DC output current	± 200	mA
I_{OP}	DC output current peak (pulse at 1 ms, 10% duty cycle)	± 400	mA
I_{CC} or I_{GND}	DC V_{CC} or ground current	± 100	mA
P_D	Power dissipation at $T_A = 70^\circ\text{C}$ ⁽¹⁾	1120	mW
T_{STG}	Storage temperature	-65 to 150	$^\circ\text{C}$
T_L	Lead temperature (10 sec)	300	$^\circ\text{C}$

1. Derate above 70 $^\circ\text{C}$ by 18.5mW/ $^\circ\text{C}$

Table 4. Recommended operating conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	1.65 to 4.5	V
V_I	Input voltage	0 to V_{CC}	V
V_{IC}	Control input voltage	0 to 4.5	V
V_O	Output voltage	0 to V_{CC}	V
T_{op}	Operating temperature	-40 to 85	$^\circ\text{C}$
dt/dv	Input rise and fall time control input	$V_{CC} = 1.65$ to 2.7 V	0 to 20
		$V_{CC} = 3.0$ to 4.5 V	0 to 10

3 Electrical characteristics

3.1 DC electrical characteristics

Table 5. DC specifications

Symbol	Parameter	V _{CC} (V)	Test condition	Value					Unit
				T _A = 25 °C			-40 to 85 °C		
				Min	Typ	Max	Min	Max	
V _{IH}	High level input voltage	1.65 – 1.95		0.65 V _{CC}			0.65 V _{CC}		V
		2.3 – 2.5		1.2			1.2		
		2.7 – 3.0		1.3			1.3		
		3.3 – 3.6		1.4			1.4		
		4.5		1.6			1.6		
V _{IL}	Low level input voltage	1.65 – 1.95				0.40		0.40	V
		2.3 – 2.5				0.60		0.60	
		2.7 – 3.0				0.60		0.60	
		3.3 – 3.6				0.60		0.60	
		4.5				0.80		0.80	
R _{ON}	Switch ON resistance	1.8	V _S = 0 V to V _{CC} I _S = 100 mA		2.0	3.0		3.5	Ω
		2.7			1.3	1.6		1.8	
		3.0			1.2	1.5		1.7	
		4.5			1.0	1.2		1.4	
ΔR _{ON}	ON resistance match between channels ⁽¹⁾	1.8	V _S at R _{ON} max I _S = 100 mA		0.06				Ω
		2.7			0.05				
		3.0			0.05				
		4.5			0.05				
R _{FLAT}	ON resistance flatness ⁽²⁾	1.8	V _S = 0 V to V _{CC} I _S = 100 mA		1.0	1.5		1.5	Ω
		2.7			0.45	0.60		0.70	
		3.0			0.43	0.50		0.60	
		4.5			0.39	0.50		0.60	
I _{OFF}	OFF state leakage current (SN), (D)	4.3	V _S = 0.3 or 4 V			±20		±100	nA
I _{IN}	Input leakage current	0 – 5.0	V _{SEL} = 0 to 4.5 V			±0.1		±1	μA
I _{CC}	Quiescent supply current	1.65 – 5.0	V _{SEL} = V _{CC} or GND			±0.05		±0.2	μA

Table 5. DC specifications (continued)

Symbol	Parameter	V _{CC} (V)	Test conditions	Value					Unit
				T _A = 25 °C			-40 to 85 °C		
				Min	Typ	Max	Min	Max	
I _{CCLV}	Quiescent supply current low voltage driving	4.3	V _{SEL} = 1.65 V		±17	±35		±70	μA
		4.3	V _{SEL} = 1.80 V		±15	±30		±60	
		4.3	V _{SEL} = 2.60 V		±5	±10		±20	

1. $\Delta R_{ON} = R_{ON(Max)} - R_{ON(Min)}$
2. Flatness is defined as the difference between the maximum and minimum value of ON resistance as measured over the specified analog signal ranges.

3.2 AC electrical characteristics

Table 6. AC electrical characteristics (C_L = 35 pF, R_L = 50 Ω, t_r = t_f ≤ 5 ns)

Symbol	Parameter	V _{CC} (V)	Test conditions	Value					Unit
				T _A = 25 °C			- 40 to 85 °C		
				Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation delay	1.65 – 1.95			0.15				ns
		2.3 – 2.7			0.14				
		3.0 – 3.3			0.13				
		3.6 – 5.0			0.13				
t _{ON}	Turn-ON time	1.65 – 1.95	V _S = 0.8 V		36				ns
		2.3 – 2.7	V _S = 1.5 V		31	40		45	
		3.0 – 3.3			24	31		40	
		3.6 – 5.0			21	28		32	
t _{OFF}	Turn-OFF time	1.65 – 1.95	V _S = 0.8		29				ns
		2.3 – 2.7	V _S = 1.5 V		17	27		37	
		3.0 – 3.3			12	23		33	
		3.6 – 5.0			11	21		31	
t _D	Break-before-make time delay	1.65 – 1.95	C _L = 35 pF R _L = 50 Ω V _S = 1.5 V		15				ns
		2.3 – 2.7			10				
		3.0 – 3.3			8				
		3.6 – 5.0			6				
Q	Charge injection	1.65	C _L = 100pF V _{GEN} = 0 V R _{GEN} = 0 Ω		16				pC
		2.3			22				
		3			26				
		5.0			33				

3.3 Analog switch characteristics

Table 7. Analog switch characteristics ($C_L = 5 \text{ pF}$, $R_L = 50 \text{ } \Omega$, $T_A = 25 \text{ } ^\circ\text{C}$)

Symbol	Parameter	V_{CC} (V)	Test conditions	Value					Unit
				$T_A = 25 \text{ } ^\circ\text{C}$			$-40 \text{ to } 85 \text{ } ^\circ\text{C}$		
				Min	Typ	Max	Min	Max	
OIRR	Off isolation ⁽¹⁾	1.65 – 5.0	$V_S = 1 \text{ V}_{RMS}$ $f = 100 \text{ kHz}$		-75				dB
Xtalk	Crosstalk	1.6 – 5.0	$V_S = 1 \text{ V}_{RMS}$ $f = 100 \text{ kHz}$		-80				dB
THD	Total harmonic distortion	2.3 – 5.0	$R_L = 600 \text{ } \Omega$ $V_S = 2 \text{ V}_{PP}$ $f = 20 \text{ Hz to } 20 \text{ kHz}$		0.03				%
BW	-3dB bandwidth	1.65 – 5.0	$R_L = 50 \text{ } \Omega$		150				MHz
C_{IN}	Control pin input capacitance				6				pF
C_{ON}	Sn port capacitance when switch is enabled	3.3	$f = 1 \text{ MHz}$		52				
C_{OFF}	Sn port capacitance when switch is disabled	3.3	$f = 1 \text{ MHz}$		25				
C_D	D port capacitance when switch is enabled	3.3	$f = 1 \text{ MHz}$		50				

1. OFF isolation = $20 \log_{10} (V_D/V_S)$, V_D = output. V_S = input to OFF switch.

4 Test circuits

Figure 3. ON resistance

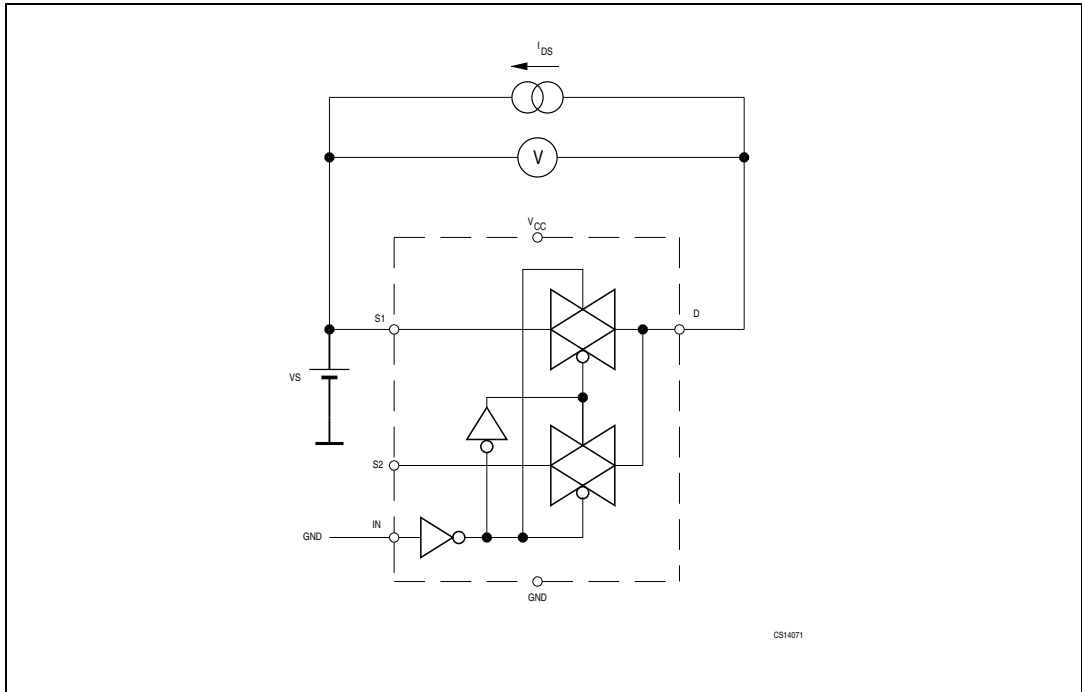


Figure 4. Bandwidth

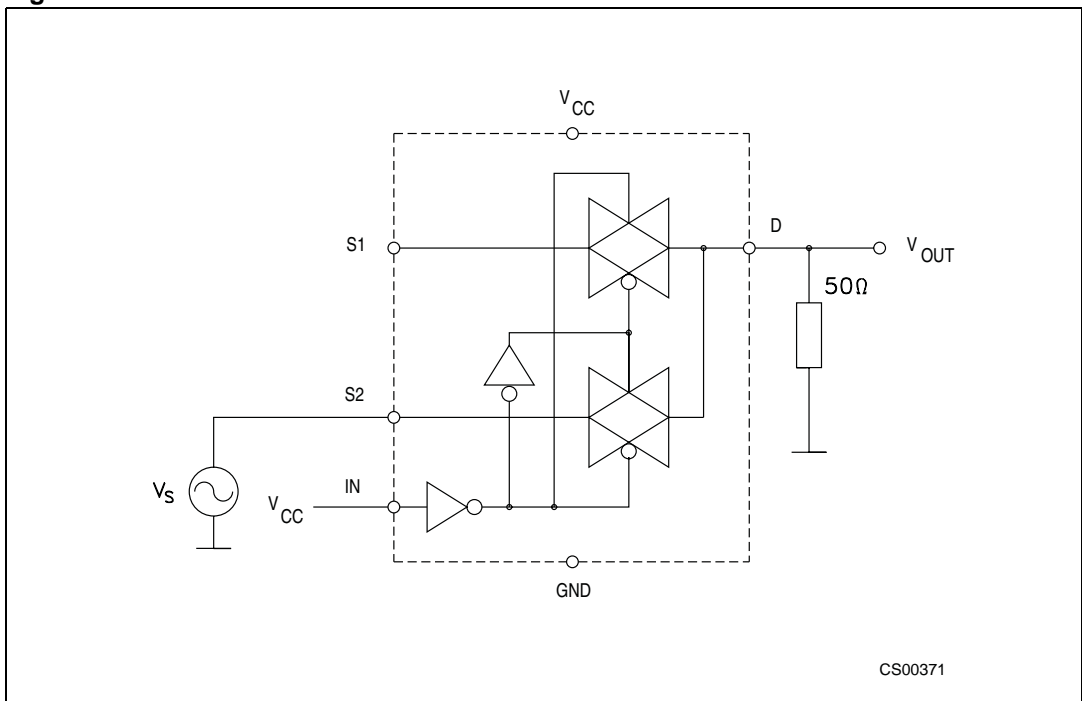


Figure 5. OFF leakage

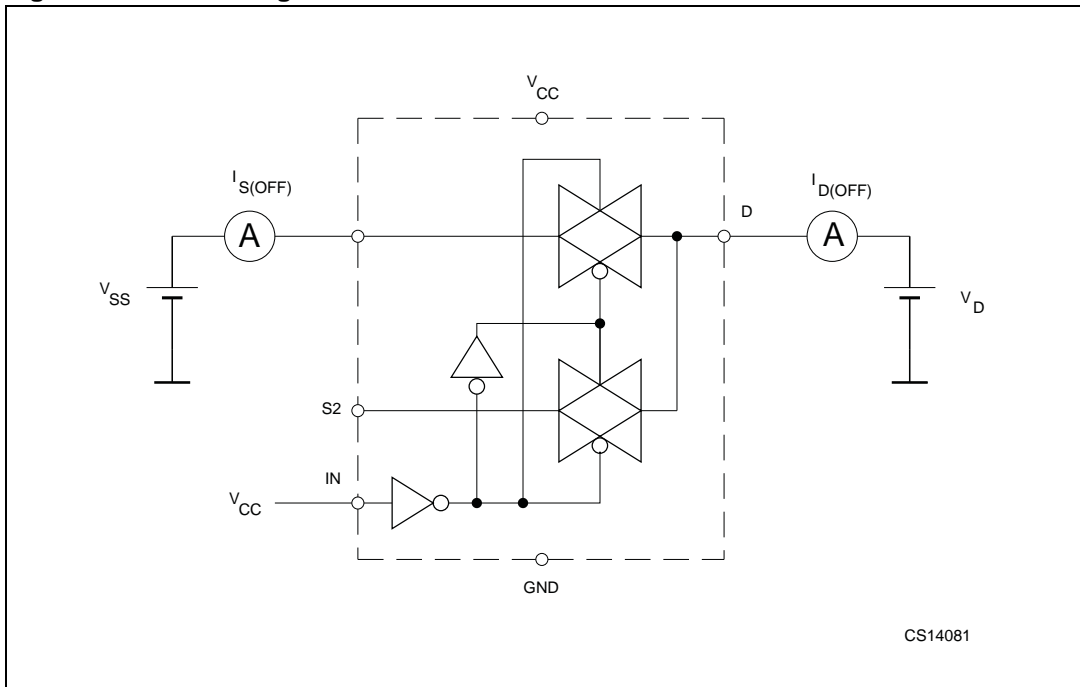


Figure 6. Channel-to-channel crosstalk

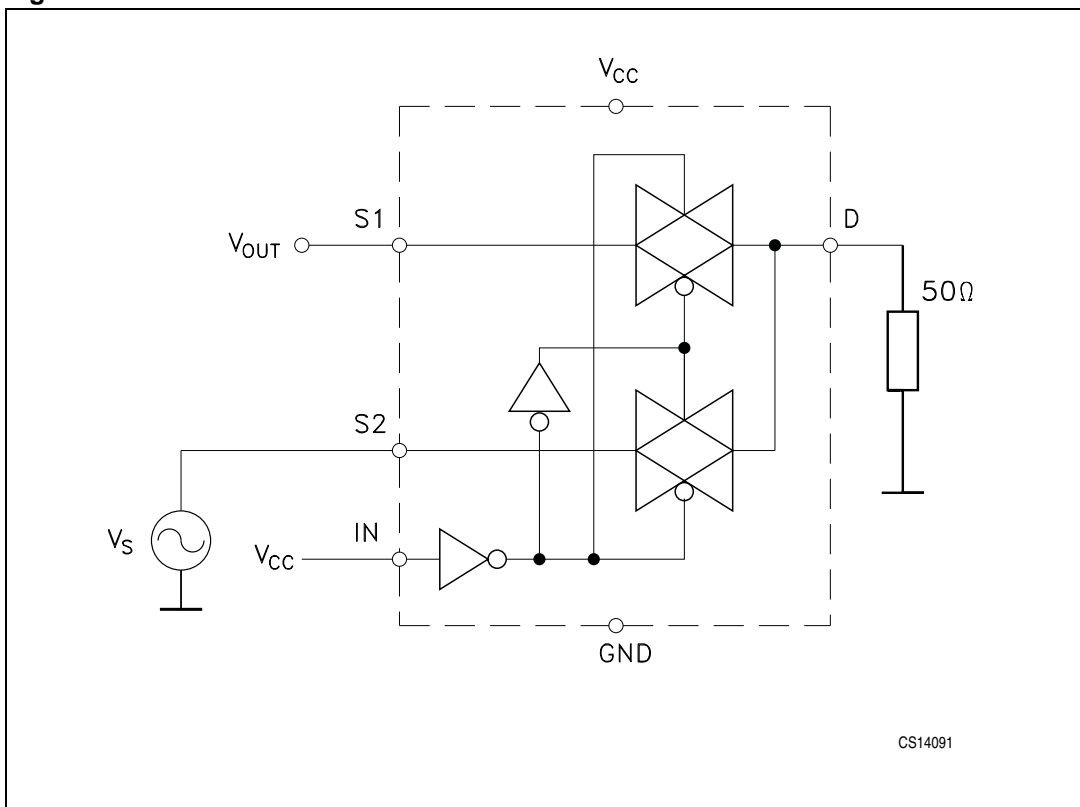


Figure 7. OFF isolation

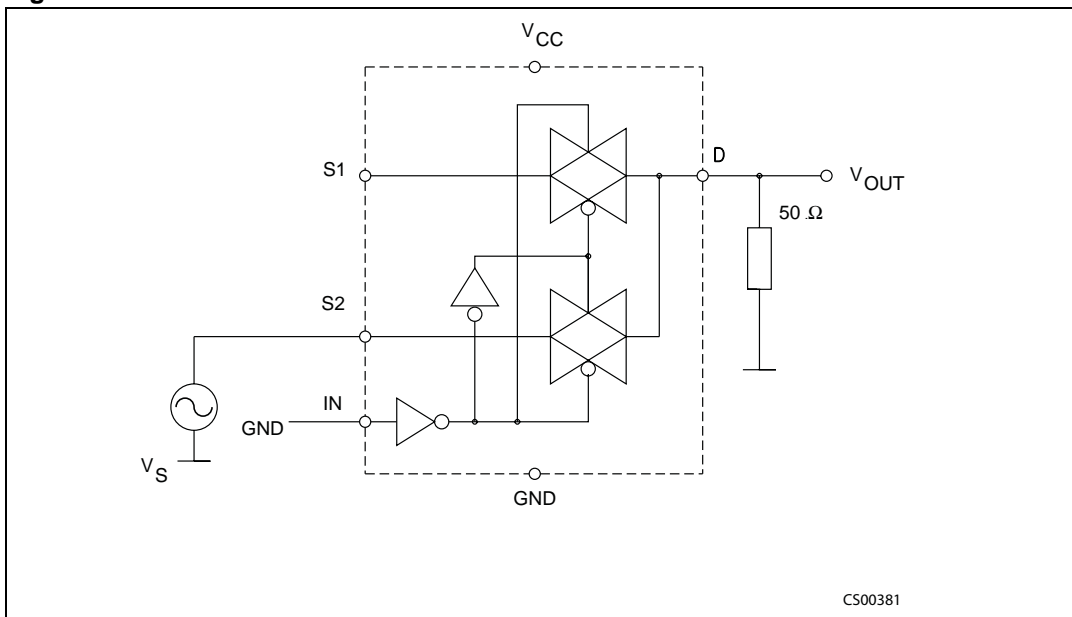
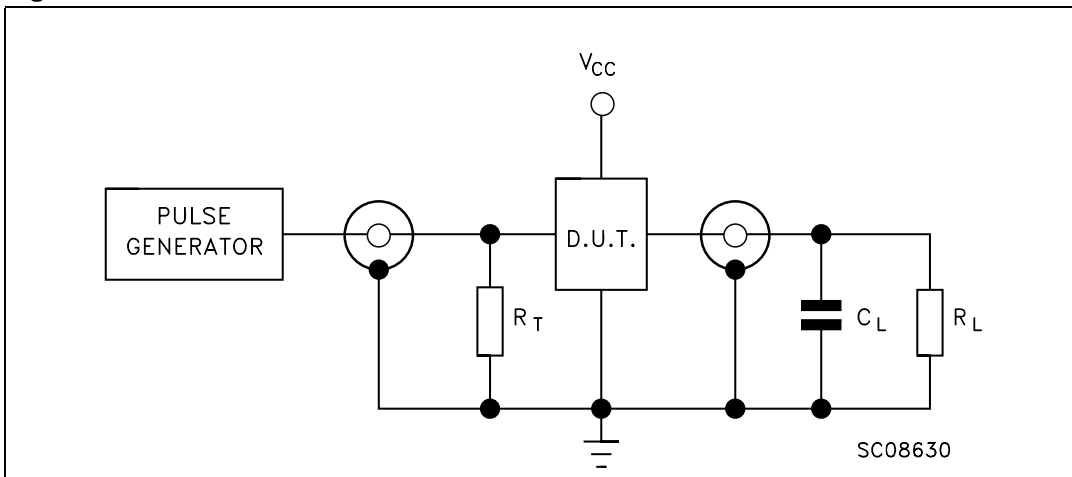


Figure 8. Test circuit



1. $C_L = 5/35$ pF or equivalent: (includes jig capacitance)
2. $R_L = 50 \Omega$ or equivalent
3. $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

Figure 9. Break-before-make time delay

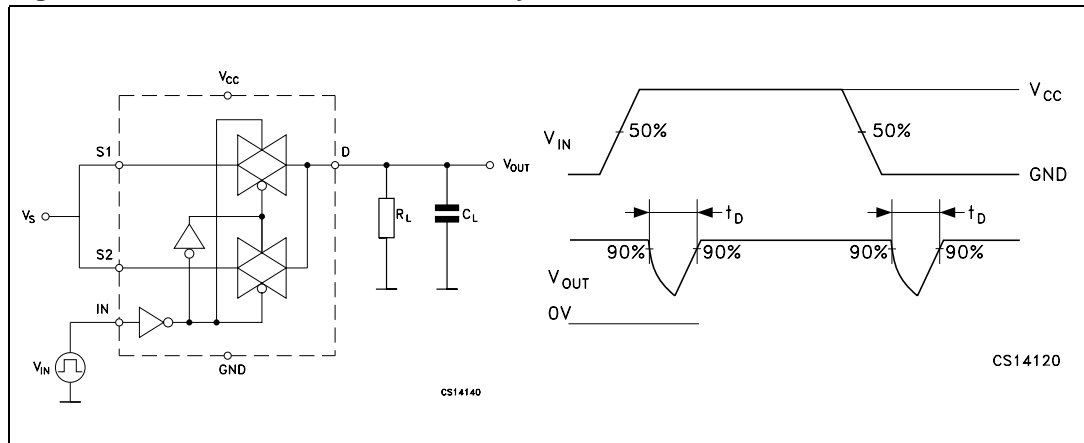


Figure 10. Switching time and charge injection
 ($V_{GEN} = 0\text{ V}$, $R_{GEN} = 0\ \Omega$, $R_L = 1\text{ M}\Omega$, $C_L = 100\text{ pF}$)

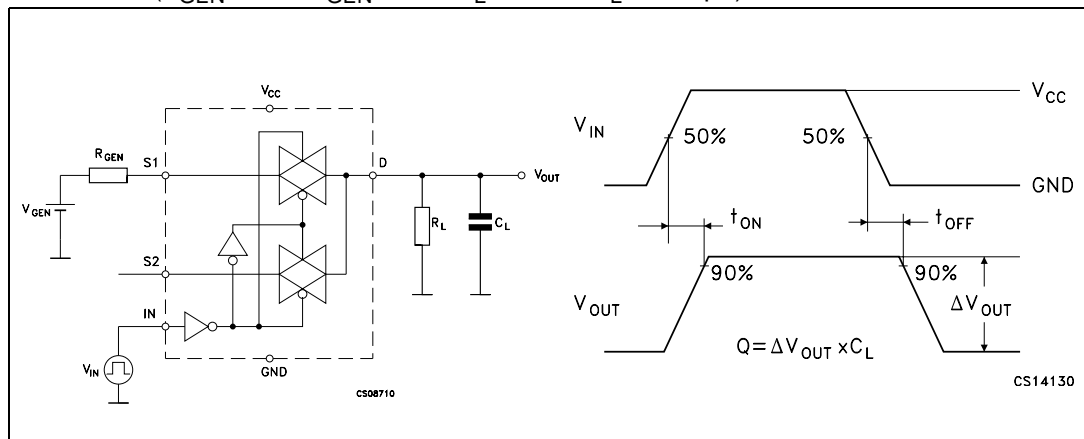
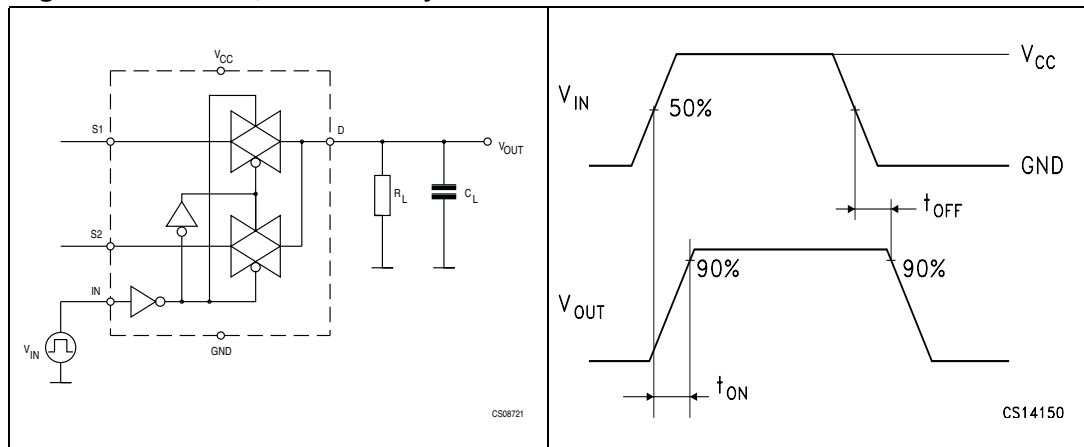


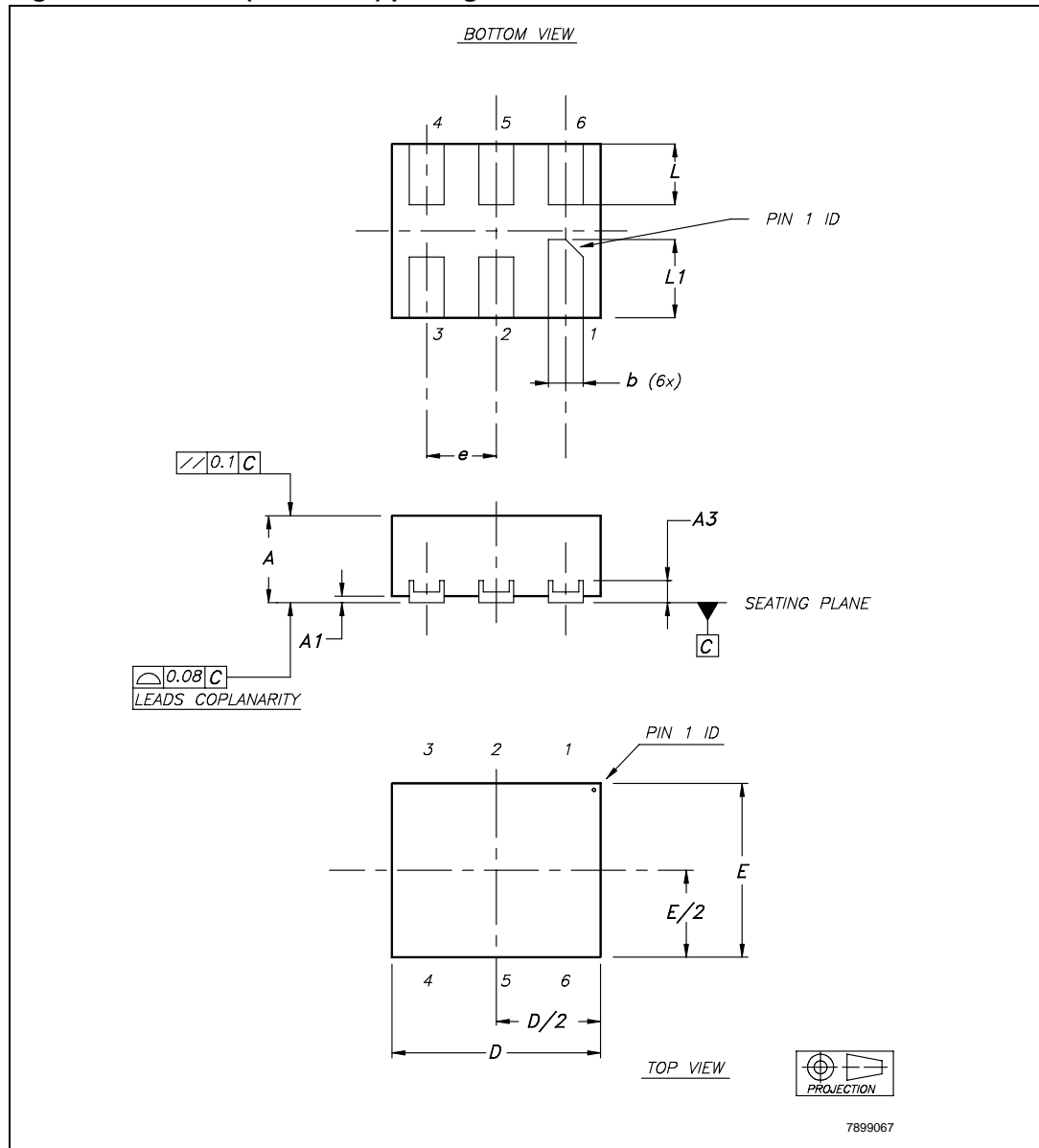
Figure 11. Turn on, turn off delay time



5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK[®] packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Figure 12. DFN6L (1.2 x 1mm) package outline



1. Drawing not to scale.

Table 8. DFN6L (1.2 x 1 mm) mechanical data

Symbol	millimeters		
	Typ	Min	Max
A	0.50	0.45	0.55
A1	0.02	0	0.05
A3	0.127		
b	0.20	0.15	0.25
D	1.20	1.15	1.25
E	1	0.95	1.05
e	0.40		
L	0.35	0.30	0.40
L1	0.45	0.40	0.50

Figure 13. DFN6L (1.2 x 1 mm) foot print recommendation

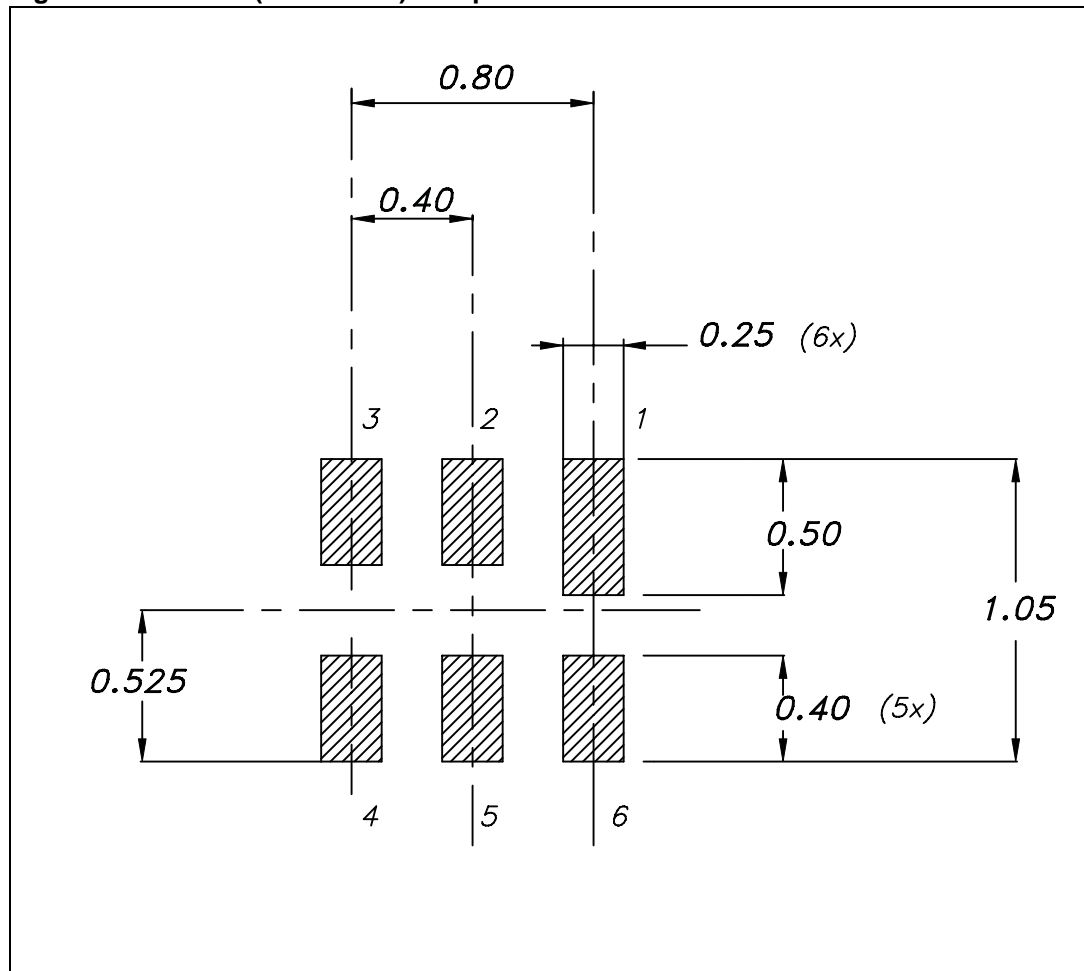
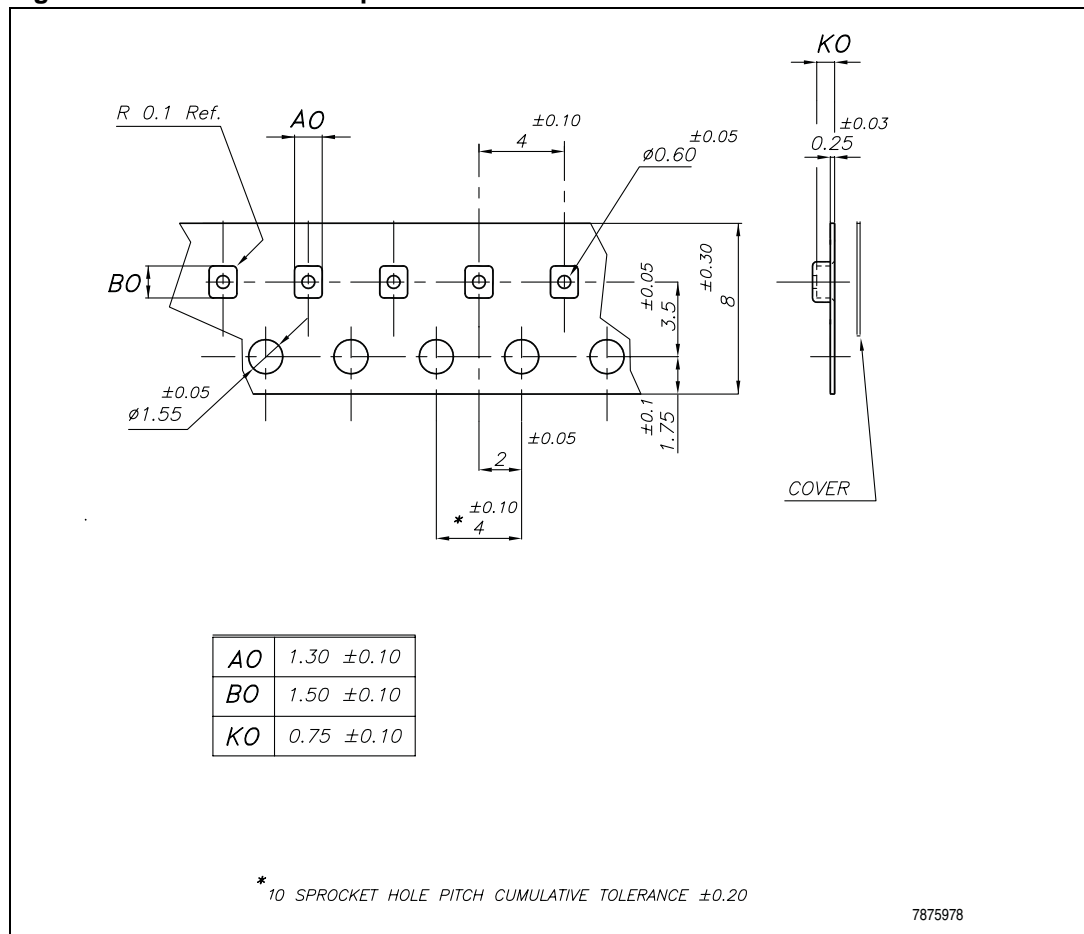
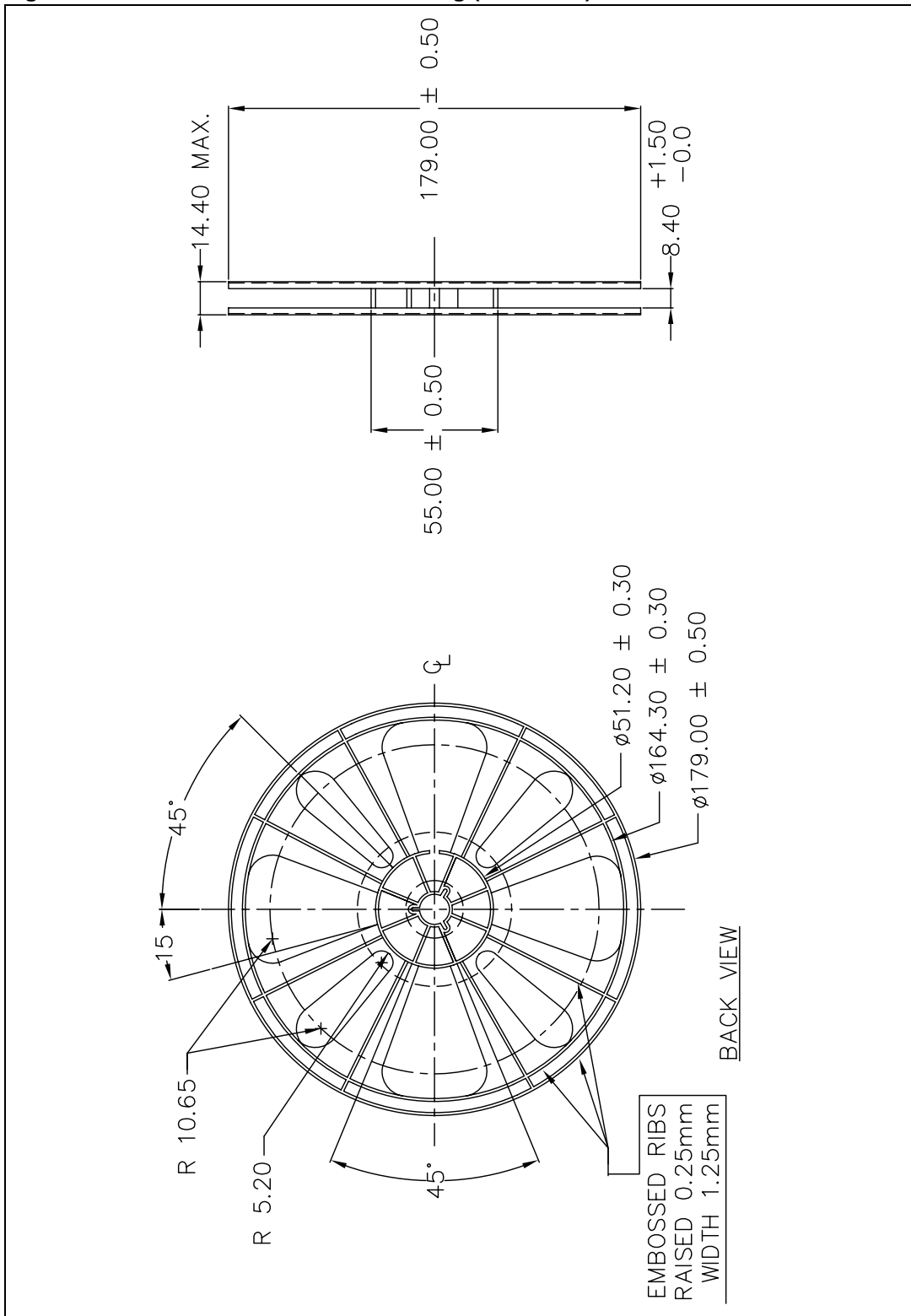


Figure 14. DFN6L carrier tape information



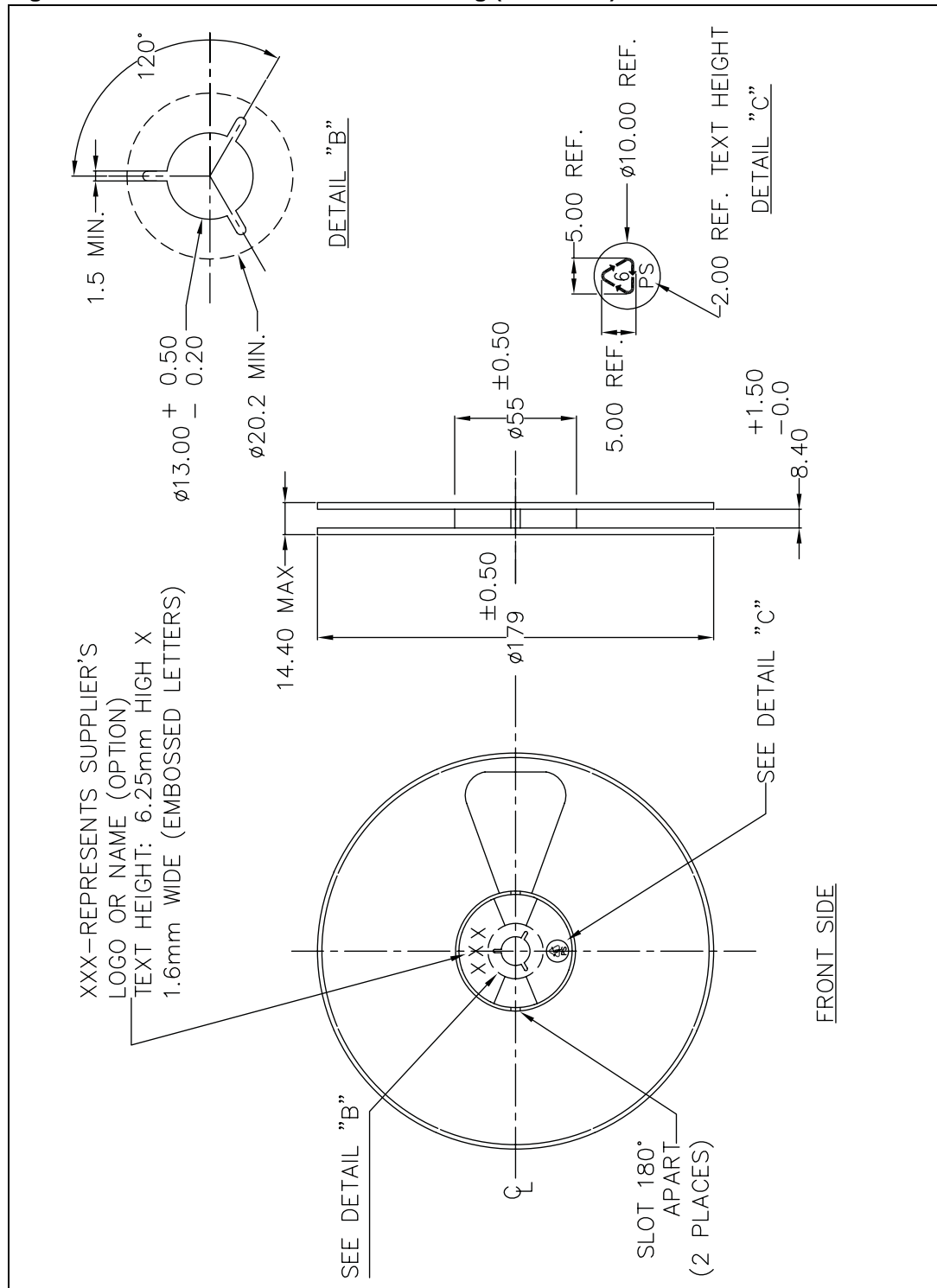
1. Drawing not to scale.
2. Dimensions are in millimeters.

Figure 15. DFN6L reel information drawing (back view)



1. Drawing not to scale.
2. Dimensions are in millimeters.

Figure 16. DFN6L reel information drawing (front view)



1. Drawing not to scale.
2. Dimensions are in millimeters.

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
30-Oct-2007	1	Initial release

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